

## **RFPD2580**

# 45MHz to 1200MHz GaAs/GaN POWER DOUBLER HYBRID

Package: SOT-115J



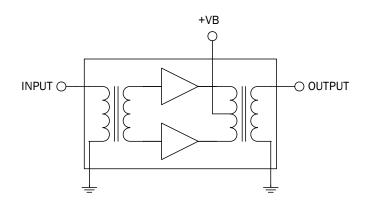


## **Features**

- Excellent Linearity
- Superior Return Loss Performance
- Extremely Low Distortion
- Optimal Reliability
- Low Noise
- Unconditionally Stable Under All Terminations
- Extremely High Output Capability
- 22.5dB Min. Gain at 1200MHz
- 450mA Max. at 24V<sub>DC</sub>

## **Applications**

 45 MHz to 1200 MHz CATV Amplifier Systems



Functional Block Diagram

## **Product Description**

The RFPD2580 is a Hybrid Power Doubler amplifier module. The part employs GaAs pHEMT die and GaN HEMT die, has high output capability, and operates from 45 MHz to 1200 MHz. It provides excellent linearity and superior return loss performance with low noise and optimal reliability.

## **Ordering Information**

RFPD2580 45 MHz to 1200 MHz GaAs/GaN Power Doubler Hybrid

## **Optimum Technology Matching® Applied**

☐ GaAs HBT	☐ SiGe BiCMOS	☑ GaAs pHEMT	✓ GaN HEMT
☐ GaAs MESFET	☐ Si BiCMOS	☐ Si CMOS	☐ BiFET HBT
☐ InGaP HBT	☐ SiGe HBT	☐ Si BJT	☐ LDMOS

## **RFPD2580**



#### **Absolute Maximum Ratings**

Parameter	Rating	Unit
RF Input Voltage (single tone)	55	dBmV
DC Supply Over-Voltage (5 minutes)	30	V
Storage Temperature	-40 to +100	°C
Operating Mounting Base Temperature	-30 to +100	°C



#### Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EUDirective 2002/95/EC (at time of this document revision).

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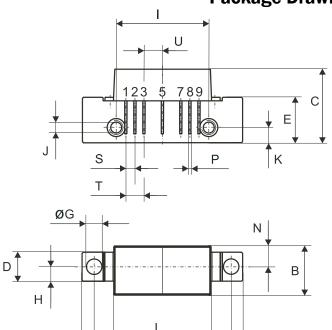
Parameter -	Specification		I locit	Condition	
Parameter	Min. Typ. Max. Unit		Unit	Condition	
Overall					$V_B = 24V, T_{MB} = 30$ °C, $Z_S = Z_L = 75\Omega$
Power Gain	21.0	21.5	22.0	dB	f=45MHz
	22.5	23.0	24.0	dB	f=1200MHz
Slope [1]	1.0	1.5	2.5	dB	f=45MHz to 1200MHz
Flatness of Frequency Response			0.8	dB	f=45MHz to 1200MHz
Input Return Loss	-20			dB	f=45 MHz to 320 MHz
	-19			dB	f=320MHz to 640MHz
	-17			dB	f=640MHz to 870MHz
	-16			dB	f=870MHz to 1000MHz
	-15			dB	f=1000MHz to 1200MHz
Output Return Loss	-20			dB	f=45MHz to 320MHz
	-19			dB	f=320MHz to 640MHz
	-18			dB	f=640MHz to 870MHz
	-17			dB	f=870MHz to 1000MHz
	-16			dB	f=1000MHz to 1200MHz
Noise Figure		3.5	4.5	dB	f=50MHz to 1200MHz
Total Current Consumption (DC)		420.0	450.0	mA	
Distortion Data 40 MHz to 550 MHz					$\label{eq:VB} \begin{aligned} &V_B=24\text{V, T}_{\text{MB}}=30^{\circ}\text{C, Z}_{\text{S}}=Z_{\text{L}}=75\Omega,\\ &\text{Vo}=56.4\text{dBmV at }1000\text{MHz, }13.4\text{dB extrapolated}\\ &\text{tilt, 79 analog channels plus 75 digital channels (-6dB offset)}^{[2]} \end{aligned}$
СТВ		-77	-74	dBc	
XMOD		-71	-68	dBc	
CSO CSO		-71	-68	dBc	
CIN	63	66		dB	

<sup>1.</sup> The slope is defined as the difference between the gain at the start frequency and the gain at the stop frequency.

2. 79 analog channels, NTSC frequency raster: 55.25 MHz to 547.25 MHz, +43 dBmV to +50 dBmV tilted output level, plus 75 digital channels, -6 dB offset relative to the equivalent analog carrier. Composite Second Order (CSO) - The CSO parameter (both sum and difference products) is defined by the NCTA. Cross Modulation (XMOD) - Cross modulation (XMOD) is measured at baseband (selective voltmeter method), referenced to 100% modulation of the carrier being tested. Carrier to Intermodulation Noise (CIN) - The CIN parameter is defined by ANSI/SCTE 17 (Test procedure for carrier to noise).

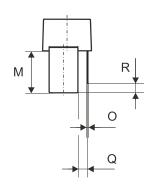


## **Package Drawing**



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scale						
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Pinning:								
1	2	3	4	5	6	7	8	9
INPUT	GND	GND		+VB		GND	GND	OUTPUT

Notes:



### All Dimensions in mm:

	nominal	min	max
Α	44,6 <sup>± 0,2</sup>	44,4	44,8
В	13,6 <sup>± 0,2</sup>	13,4	13,8
С	20,4 <sup>± 0,5</sup>	19,9	20,9
D	8 <sup>± 0,15</sup>	7,85	8,15
Е	12,6 <sup>± 0,15</sup>	12,45	12,75
F	38,1 ± 0,2	37,9	38,3
G	4 +0,2 / -0,05	3,95	4,2
Н	4 <sup>± 0,2</sup>	3,8	4,2
-1	25,4 <sup>± 0,2</sup>	25,2	25,6
J	UNC 6-32	-	-
K	4,2 <sup>± 0,2</sup>	4,0	4,4
L	27,2 <sup>± 0,2</sup>	27,0	27,4
М	11,6 <sup>± 0,5</sup>	11,1	12,1
Ν	5,8 <sup>± 0,4</sup>	5,4	6,2
0	0,25 <sup>± 0,02</sup>	0,23	0,27
Р	0,45 <sup>± 0,03</sup>	0,42	0,48
Q	2,54 <sup>± 0,3</sup>	2,24	2,84
R	2,54 <sup>± 0,5</sup>	2,04	3,04
S	2,54 <sup>± 0,25</sup>	2,29	2,79
Т	5,08 <sup>± 0,25</sup>	4,83	5,33
U	5,08 <sup>± 0,25</sup>	4,83	5,33
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